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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Obsolete
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	64
Program Memory Size	192KB (192K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 17x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	80-LQFP
Supplier Device Package	80-LFQFP (12x12)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f101mhafb-v0

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Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

RL78/G13 1. OUTLINE

Table 1-1. List of Ordering Part Numbers

(12/12)

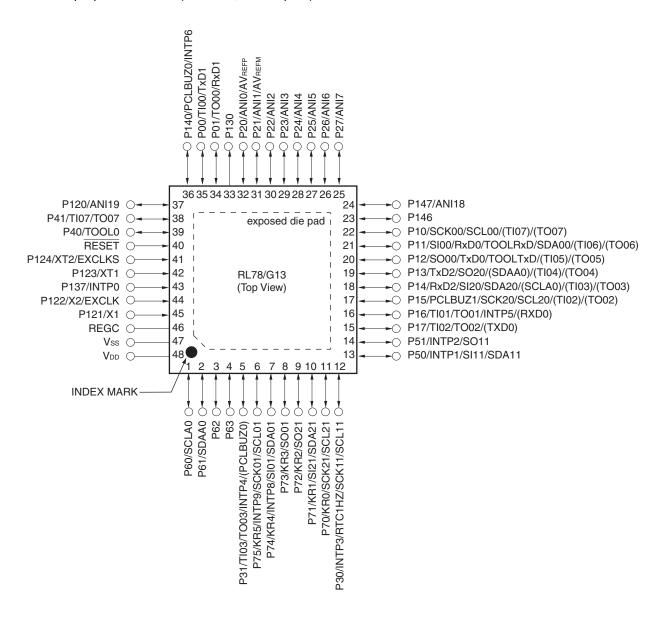
Pin count	Package	Data flash	Fields of Application Note	Ordering Part Number
128 pins	128-pin plastic LFQFP (14 × 20 mm, 0.5 mm pitch)	Mounted	A D	R5F100SHAFB#V0, R5F100SJAFB#V0, R5F100SKAFB#V0, R5F100SLAFB#V0 R5F100SHAFB#X0, R5F100SJAFB#X0, R5F100SKAFB#X0, R5F100SLAFB#X0 R5F100SHDFB#V0, R5F100SJDFB#V0, R5F100SKDFB#V0, R5F100SJDFB#V0 R5F100SHDFB#X0, R5F100SJDFB#X0.
				R5F100SKDFB#X0, R5F100SLDFB#X0
		Not mounted	A	R5F101SHAFB#V0, R5F101SJAFB#V0, R5F101SKAFB#V0, R5F101SLAFB#V0 R5F101SHAFB#X0, R5F101SJAFB#X0, R5F101SKAFB#X0, R5F101SLAFB#X0
			D	R5F101SHDFB#V0, R5F101SJDFB#V0, R5F101SKDFB#V0, R5F101SLDFB#V0 R5F101SHDFB#X0, R5F101SJDFB#X0, R5F101SKDFB#X0, R5F101SLDFB#X0

Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.

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• 48-pin plastic HWQFN (7 × 7 mm, 0.5 mm pitch)



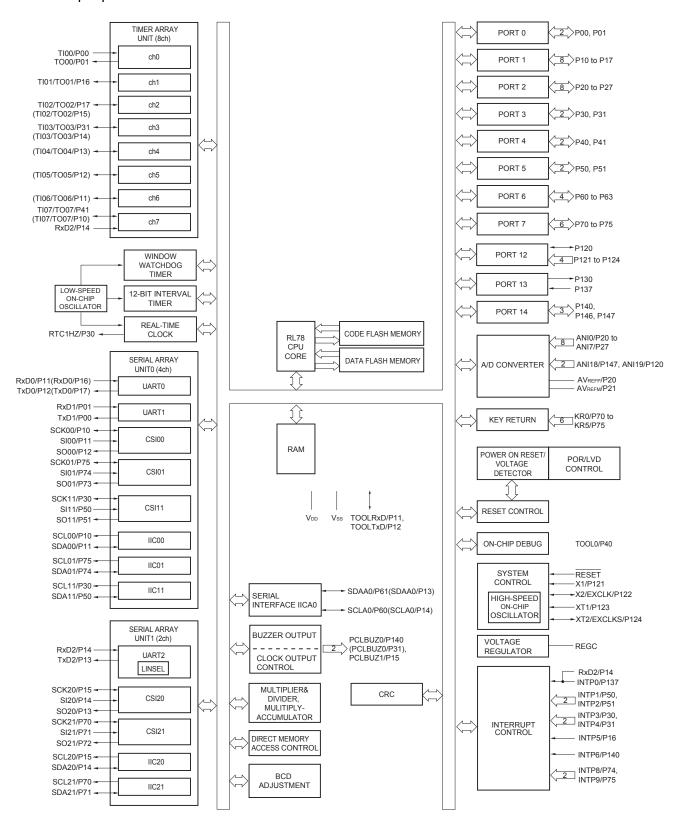
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to $V_{\rm ss.}$

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1.5.9 48-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (4/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Output voltage, Voh	V _{OH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -10.0 mA	EV _{DD0} –			V
		to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to	$4.0 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -3.0 mA	EV _{DD0} – 0.7			V
		P117, P120, P125 to P127, P130, P140 to P147	$2.7 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V},$ Iон1 = -2.0 mA	EV _{DD0} – 0.6			V
			$\label{eq:loss_loss} \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ \\ I_{\text{OH1}} = -1.5 \ mA \end{array}$	EV _{DD0} – 0.5			٧
			$1.6 \text{ V} \le \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $I_{\text{OH1}} = -1.0 \text{ mA}$	EV _{DD0} – 0.5			V
	V _{OH2}	P20 to P27, P150 to P156	1.6 V \leq V _{DD} \leq 5.5 V, I _{OH2} = $-100~\mu$ A	V _{DD} - 0.5			V
Output voltage, low	V _{OL1}	P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 20~mA$			1.3	٧
			$\label{eq:loss_loss} \begin{cases} 4.0 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}, \\ \\ \text{Iol1} = 8.5 \text{ mA} \end{cases}$			0.7	>
			$2.7~V \leq EV_{\text{DD0}} \leq 5.5~V,$ $I_{\text{OL1}} = 3.0~\text{mA}$			0.6	>
			$2.7~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL1} = 1.5~mA$			0.4	V
			$\label{eq:loss_state} \begin{array}{l} 1.8 \ V \leq EV_{\text{DD0}} \leq 5.5 \ V, \\ \\ I_{\text{OL1}} = 0.6 \ mA \end{array}$			0.4	V
			$1.6~V \leq EV_{DD0} < 5.5~V,$ $I_{OL1} = 0.3~mA$			0.4	V
	V _{OL2}	P20 to P27, P150 to P156	1.6 V \leq VDD \leq 5.5 V, lol2 = 400 μ A			0.4	V
	Vol3	P60 to P63	$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 15.0~mA$			2.0	٧
			$4.0~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 5.0~mA$			0.4	V
			$2.7~\textrm{V} \leq \textrm{EV}_\textrm{DD0} \leq 5.5~\textrm{V},$ $\textrm{Iol3} = 3.0~\textrm{mA}$			0.4	V
		$1.8~V \leq EV_{DD0} \leq 5.5~V,$ $I_{OL3} = 2.0~mA$			0.4	V	
			$1.6 \text{ V} \leq \text{EV}_{\text{DD0}} < 5.5 \text{ V},$ $\text{Iol3} = 1.0 \text{ mA}$			0.4	V

Caution P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 do not output high level in N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVSSD, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - **4.** When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 16 \text{ MHz}$ LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 8 \text{ MHz}$ LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 4 \text{ MHz}$

- **8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

(4) Peripheral Functions (Common to all products)

$(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Low-speed on- chip oscillator operating current	IFIL ^{Note 1}				0.20		μΑ
RTC operating current	RTC Notes 1, 2, 3				0.02		μА
12-bit interval timer operating current	IIT Notes 1, 2, 4				0.02		μΑ
Watchdog timer operating current	IWDT Notes 1, 2, 5	fıL = 15 kHz			0.22		μА
A/D converter	IADC Notes 1, 6	When	Normal mode, AV _{REFP} = V _{DD} = 5.0 V		1.3	1.7	mA
operating current		conversion at maximum speed	Low voltage mode, AVREFP = VDD = 3.0 V		0.5	0.7	mA
A/D converter reference voltage current	IADREF Note 1				75.0		μА
Temperature sensor operating current	ITMPS Note 1				75.0		μΑ
LVD operating current	LVI Notes 1, 7				0.08		μА
Self- programming operating current	FSP Notes 1, 9				2.50	12.20	mA
BGO operating current	BGO Notes 1, 8				2.50	12.20	mA
SNOOZE	ISNOZ Note 1	ADC operation	The mode is performed Note 10		0.50	0.60	mA
operating current			The A/D conversion operations are performed, Low voltage mode, $AV_{\text{REFP}} = V_{\text{DD}} = 3.0 \text{ V}$		1.20	1.44	mA
		CSI/UART opera	tion		0.70	0.84	mA

Notes 1. Current flowing to VDD.

- 2. When high speed on-chip oscillator and high-speed system clock are stopped.
- 3. Current flowing only to the real-time clock (RTC) (excluding the operating current of the low-speed onchip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IRTC, when the real-time clock operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added. IDD2 subsystem clock operation includes the operational current of the real-time clock.
- 4. Current flowing only to the 12-bit interval timer (excluding the operating current of the low-speed on-chip oscillator and the XT1 oscillator). The supply current of the RL78 microcontrollers is the sum of the values of either IDD1 or IDD2, and IIT, when the 12-bit interval timer operates in operation mode or HALT mode. When the low-speed on-chip oscillator is selected, IFIL should be added.
- **5.** Current flowing only to the watchdog timer (including the operating current of the low-speed on-chip oscillator). The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and IWDT when the watchdog timer is in operation.



2.4 AC Characteristics

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Items	Symbol		Conditions	·	MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсч	Main	HS (high-	$2.7V\!\leq\!V_{DD}\!\leq\!5.5V$	0.03125		1	μS
instruction execution time)		system clock (fmain)	speed main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		operation	LS (low-speed main) mode	$1.8 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.125		1	μS
			LV (low- voltage main) mode	1.6 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μS
		Subsystem of	clock (fsuв)	1.8 V ≤ V _{DD} ≤ 5.5 V	28.5	30.5	31.3	μS
		operation						
		In the self	HS (high-	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
		programming mode	speed main) mode	$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
			LS (low-speed main) mode	$1.8 V \le V_{DD} \le 5.5 V$	0.125		1	μS
			LV (low- voltage main) mode	1.8 V ≤ V _{DD} ≤ 5.5 V	0.25		1	μS
External system clock	fex	2.7 V ≤ V _{DD} ≤	≤ 5.5 V		1.0		20.0	MHz
frequency		2.4 V ≤ V _{DD} <			1.0		16.0	MHz
		1.8 V ≤ V _{DD} <	< 2.4 V		1.0		8.0	MHz
		1.6 V ≤ V _{DD} < 1.8 V		1.0		4.0	MHz	
	fexs				32		35	kHz
External system clock input	texh, texl	$2.7~V \leq V_{DD} \leq 5.5~V$		24			ns	
high-level width, low-level width		2.4 V ≤ V _{DD} <	< 2.7 V		30			ns
		1.8 V ≤ V _{DD} <	< 2.4 V		60			ns
		1.6 V ≤ V _{DD} <	< 1.8 V		120			ns
	texhs, texhs				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tтіL				1/fмск+10			ns ^{Note}
TO00 to TO07, TO10 to TO17	fто	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			1.8 V	≤ EV _{DD0} < 2.7 V			4	MHz
			1.6 V	≤ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spec	ed 1.8 V	$\leq EV_{DD0} \leq 5.5 V$			4	MHz
		main) mode	1.6 V	≤ EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode	age 1.6 V	\leq EV _{DD0} \leq 5.5 V			2	MHz
PCLBUZ0, PCLBUZ1 output	fpcL	HS (high-spe	eed 4.0 V	$\leq EV_{DD0} \leq 5.5 V$			16	MHz
frequency		main) mode		≤ EV _{DD0} < 4.0 V			8	MHz
				\leq EV _{DD0} $<$ 2.7 V			4	MHz
				≤ EV _{DD0} < 1.8 V			2	MHz
		LS (low-spec		\leq EV _{DD0} \leq 5.5 V			4	MHz
		main) mode	_	≤ EV _{DD0} < 1.8 V			2	MHz
		LV (low-volta main) mode		\leq EV _{DD0} \leq 5.5 V \leq EV _{DD0} $<$ 1.8 V			2	MHz MHz
Interrupt input high-level width,	tinth,	INTP0		≤ V _{DD} ≤ 5.5 V	1		=	μS
low-level width	tintl	INTP1 to INT		≤ EV _{DD0} ≤ 5.5 V	1			μS
Karrintanının tianın tarınlarınl	tkr	KR0 to KR7		≤ EV _{DD0} ≤ 5.5 V	250			ns
Key interrupt input low-level					1		1	
Key interrupt input low-level width			1.6 V	≤ EV _{DD0} < 1.8 V	1			μS

(Note and Remark are listed on the next page.)



220

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(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (2/2)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$ Parameter Symbo Conditions HS (high-speed LS (low-speed main) LV (low-voltage main) Unit main) Mode ı Mode Mode MIN. MIN. MAX. MIN. MAX. MAX. Slp setup time tsik2 $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$ $1/f_{MCK}+2$ 1/fmck+30 1/fmck+30 ns (to SCKp↑) Note 1 n $1.8~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+3 1/fмск+30 1/fмcк+30 ns 0 $1.7~V \leq EV_{DD0} \leq 5.5~V$ 1/fмск+4 $1/f_{MCK}+40$ $1/f_{MCK}+40$ ns 0 1/fмск+40 1/fмск+40 $1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$ ns Slp hold time tks12 $1.8~V \leq EV_{DD0} \leq 5.5~V$ 1/fмcк+3 1/fмcк+31 1/fмcк+31 ns (from SCKp↑) 1 $1.7~V \leq EV_{DD0} \leq 5.5~V$ 1/fмcк+ 1/fмск+ 1/fмcк+ ns 250 250 250 $1.6~V \leq EV_{\text{DD0}} \leq 5.5~V$ 1/fmck+ 1/fмcк+ ns 250 250 2/f_{MCK+} 2/f_{MCK+} Delay time tks02 C = 30 $2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ ns pF Note 4 from SCKp↓ to 44 110 110 SOp output Note $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ 2/fмcк+ 2/fмск+ ns 110 75 110 2/fмск+ $1.8 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fмск+ 2/fмск+ ns 110 110 110 $1.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fmck+ 2/fmck+ 2/fмск+ ns 220 220 220 $1.6 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5$ 2/fмск+ 2/fмск+ ns

- **Notes 1.** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp setup time becomes "to $SCKp\downarrow$ " when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 2. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The SIp hold time becomes "from SCKp↓" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 3. When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1. The delay time to SOp output becomes "from SCKp↑" when DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.
 - 4. C is the load capacitance of the SOp output lines.
 - 5. Transfer rate in the SNOOZE mode: MAX. 1 Mbps

Caution Select the normal input buffer for the SIp pin and SCKp pin and the normal output mode for the SOp pin by using port input mode register g (PIMg) and port output mode register g (POMg).

- **Remarks 1.** p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM number (g = 0, 1, 4, 5, 8, 14)
 - 2. fmck: Serial array unit operation clock frequency

 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

 n: Channel number (mn = 00 to 03, 10 to 13))

(9) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (slave mode, SCKp... external clock input)

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (1/2)$

Parameter	Symbol	Cor	Conditions		high- main) ode	LS (low		-	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time Note 1		$4.0 \text{ V} \le \text{EV}_{DD0} \le 5.5 \text{ V},$ $2.7 \text{ V} \le \text{V}_b \le 4.0 \text{ V}$	24 MHz < fмск	14/ fмск		_		_		ns
			20 MHz < fмcκ ≤ 24 MHz	12/ fмск						ns
			8 MHz < fмcк ≤ 20 MHz	10/ fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fmck ≤ 4 MHz	6/fмск		10/ fмск		10/ fмск		ns
		$2.7 \text{ V} \le \text{EV}_{DD0} < 4.0 \text{ V},$ $2.3 \text{ V} \le \text{V}_{b} \le 2.7 \text{ V}$	24 MHz < fмск	20/ fмск		_		_		ns
			20 MHz < fмcк ≤ 24 MHz	16/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	14/ fмск		_		_		ns
			8 MHz < fмcк ≤ 16 MHz	12/ fмск		_		_		ns
			4 MHz < fмcк ≤ 8 MHz	8/fмск		16/ fмск		_		ns
			fмск ≤ 4 MHz	6/ƒмск		10/ fмск		10/ fмск		ns
		$1.8 \text{ V} \le \text{EV}_{\text{DD0}} < 3.3 \text{ V},$ $1.6 \text{ V} \le \text{V}_{\text{b}} \le 2.0 \text{ V}^{\text{Note}}$	24 MHz < fмск	48/ fмск		_		_		ns
		2	20 MHz < fмcк ≤ 24 MHz	36/ fмск		_		_		ns
			16 MHz < fмcк ≤ 20 MHz	32/ fмск		_		_		ns
			8 MHz < f _{MCK} ≤ 16 MHz	26/ fмск						ns
			4 MHz < f _{MCK} ≤ 8 MHz	16/ fмск		16/ fмск		_		ns
			fмcк ≤ 4 MHz	10/ fмск		10/ fмск		10/ fмск		ns

(Notes and Caution are listed on the next page, and Remarks are listed on the page after the next page.)

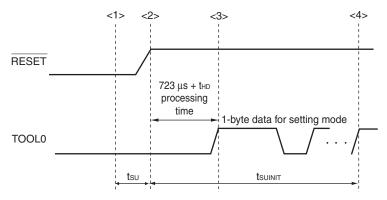
- **Notes 1.** Excludes quantization error ($\pm 1/2$ LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD} .
 - Zero-scale error/Full-scale error: Add $\pm 0.05\%FSR$ to the MAX. value when AV_{REFP} = V_{DD}.
 - Integral linearity error/ Differential linearity error: Add ± 0.5 LSB to the MAX. value when AV_{REFP} = V_{DD}.
 - **4.** Values when the conversion time is set to 57 μ s (min.) and 95 μ s (max.).
 - 5. Refer to 2.6.2 Temperature sensor/internal reference voltage characteristics.



2.10 Timing of Entry to Flash Memory Programming Modes

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.8 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V})$

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Time to complete the communication for the initial setting after the external reset is released	tsuіліт	POR and LVD reset must be released before the external reset is released.			100	ms
Time to release the external reset after the TOOL0 pin is set to the low level	tsu	POR and LVD reset must be released before the external reset is released.	10			μS
Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)	tно	POR and LVD reset must be released before the external reset is released.	1			ms



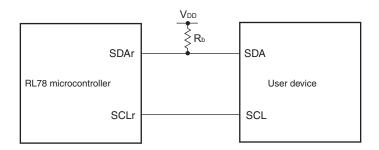
- <1> The low level is input to the TOOL0 pin.
- <2> The external reset is released (POR and LVD reset must be released before the external reset is released.).
- <3> The TOOL0 pin is set to the high level.
- <4> Setting of the flash memory programming mode by UART reception and complete the baud rate setting.

Remark tsuinit: Communication for the initial setting must be completed within 100 ms after the external reset is released during this period.

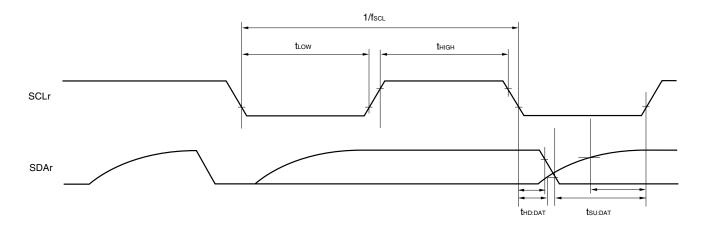
tsu: Time to release the external reset after the TOOL0 pin is set to the low level

thd: Time to hold the TOOL0 pin at the low level after the external reset is released (excluding the processing time of the firmware to control the flash memory)

Simplified I²C mode mode connection diagram (during communication at same potential)



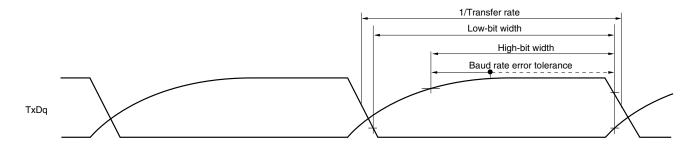
Simplified I²C mode serial transfer timing (during communication at same potential)

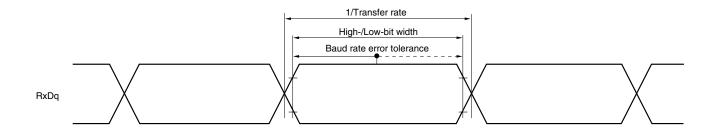


Remarks 1. $R_b[\Omega]$:Communication line (SDAr) pull-up resistance, $C_b[F]$: Communication line (SDAr, SCLr) load capacitance

- 2. r: IIC number (r = 00, 01, 10, 11, 20, 21, 30, 31), g: PIM number (g = 0, 1, 4, 5, 8, 14), h: POM number (g = 0, 1, 4, 5, 7 to 9, 14)
- 3. fmck: Serial array unit operation clock frequency
 (Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), mn = 00 to 03, 10 to 13)

UART mode bit width (during communication at different potential) (reference)





- $\begin{tabular}{ll} \textbf{Remarks 1.} & R_b[\Omega]: Communication line (TxDq) pull-up resistance, \\ & C_b[F]: Communication line (TxDq) load capacitance, V_b[V]: Communication line voltage \\ \end{tabular}$
 - **2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 8, 14)
 - 3. fmck: Serial array unit operation clock frequency(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn).m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13))
 - **4.** UART2 cannot communicate at different potential when bit 1 (PIOR1) of peripheral I/O redirection register (PIOR) is 1.

3.6 Analog Characteristics

3.6.1 A/D converter characteristics

Classification of A/D converter characteristics

		Reference Voltage					
	Reference voltage (+) = AVREFP	Reference voltage (+) = VDD	Reference voltage (+) = V _{BGR}				
Input channel	Reference voltage (–) = AVREFM	Reference voltage (-) = Vss	Reference voltage (–) = AVREFM				
ANI0 to ANI14	Refer to 3.6.1 (1) .	Refer to 3.6.1 (3) .	Refer to 3.6.1 (4) .				
ANI16 to ANI26	Refer to 3.6.1 (2) .						
Internal reference voltage	Refer to 3.6.1 (1) .		-				
Temperature sensor output							
voltage							

(1) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI2 to ANI14, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution AV _{REFP} = V _{DD} Note 3	2.4 V ≤ AVREFP ≤ 5.5 V		1.2	±3.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI2 to ANI14	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: Internal reference	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
		voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.4~V \leq V \text{DD} \leq 5.5~V$	17		39	μs
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution AVREFP = VDD Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution AV _{REFP} = V _{DD} Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±0.25	%FSR
Integral linearity error	ILE	10-bit resolution AVREFP = VDD Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±2.5	LSB
Differential linearity error	DLE	10-bit resolution AV _{REFP} = V _{DD} Note 3	$\begin{array}{c} 2.4 \ V \leq AV_{REFP} \leq 5.5 \\ V \end{array}$			±1.5	LSB
Analog input voltage	Vain	ANI2 to ANI14		0		AVREFP	V
		Internal reference voltage output (2.4 V \leq VDD \leq 5.5 V, HS (high-speed main) mode)			VBGR Note 4		V
		Temperature sensor output volume (2.4 V \leq VDD \leq 5.5 V, HS (high	· ·		VTMPS25 Note	4	V

(Notes are listed on the next page.)



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{\text{DD0}} = \text{EV}_{\text{DD1}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, 2.4 \text{ V} \le \text{AV}_{\text{REFP}} \le \text{V}_{\text{DD}} \le 5.5 \text{ V}, \text{V}_{\text{SS}} = \text{EV}_{\text{SS0}} = \text{EV}_{\text{SS1}} = 0 \text{ V}, \text{Reference voltage (+)} = \text{AV}_{\text{REFP}}, \text{Reference voltage (-)} = \text{AV}_{\text{REFM}} = 0 \text{ V})$

Parameter	Symbol	Condition	าร	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution $EV_{DD0} \leq AV_{REFP} = V_{DD}^{Notes 3, 4}$	$2.4~V \le AV_{REFP} \le 5.5$ V		1.2	±5.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin : ANI16 to ANI26	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution $EV_{DD0} \le AV_{REFP} = V_{DD}^{Notes 3, 4}$	$2.4~V \le AV_{REFP} \le 5.5$ V			±0.35	%FSR
Full-scale error ^{Notes 1, 2}	Ers	10-bit resolution $EV_{DD0} \le AV_{REFP} = V_{DD}^{Notes 3, 4}$	$2.4~V \le AV_{REFP} \le 5.5$ V			±0.35	%FSR
Integral linearity error ^{Note 1}	ILE	10-bit resolution $EVDD0 \le AV_{REFP} = V_{DD}^{Notes 3, 4}$	2.4 V ≤ AVREFP ≤ 5.5 V			±3.5	LSB
Differential linearity error	DLE	10-bit resolution $EVDD0 \le AV_{REFP} = V_{DD}^{Notes 3, 4}$	$2.4~V \le AV_{REFP} \le 5.5$ V			±2.0	LSB
Analog input voltage	Vain	ANI16 to ANI26		0		AVREFP and EVDD0	V

Notes 1. Excludes quantization error (±1/2 LSB).

- 2. This value is indicated as a ratio (%FSR) to the full-scale value.
- **3.** When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\% FSR$ to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

4. When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

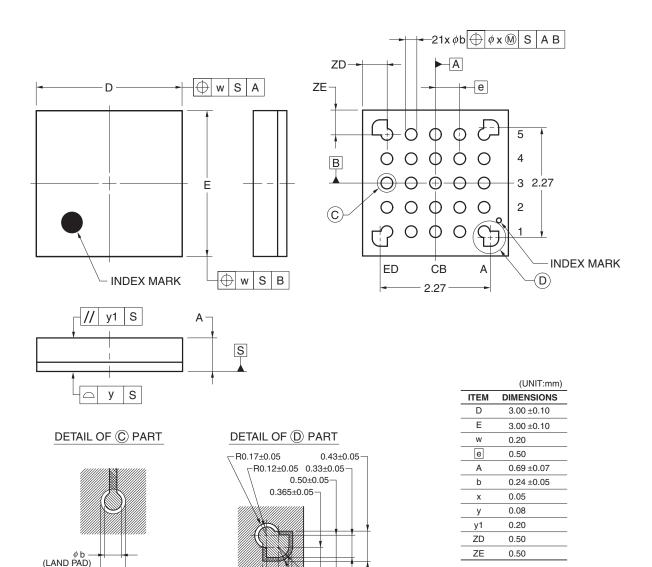
Zero-scale error/Full-scale error: Add $\pm 0.20\% FSR$ to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

4.3 25-pin Products

R5F1008AALA, R5F1008CALA, R5F1008DALA, R5F1008EALA R5F1018AALA, R5F1018CALA, R5F1018DALA, R5F1018EALA R5F1008AGLA, R5F1008CGLA, R5F1008DGLA, R5F1008EGLA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-WFLGA25-3x3-0.50	PWLG0025KA-A	P25FC-50-2N2-2	0.01



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R0.165±0.05

R0.215±0.05

0.365±0.05

0.50±0.05

0.43±0.05

φ0.34±0.05 → (APERTURE OF

SOLDER RESIST)

R5F100GAANA, R5F100GCANA, R5F100GDANA, R5F100GEANA, R5F100GFANA, R5F100GHANA, R5F100GHANA, R5F100GKANA, R5F100GKANA, R5F100GKANA, R5F100GKANA

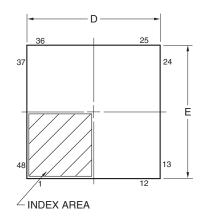
R5F101GAANA, R5F101GCANA, R5F101GDANA, R5F101GEANA, R5F101GFANA, R5F101GHANA, R5F101GHANA, R5F101GHANA, R5F101GKANA, R5F101GKANA, R5F101GLANA

R5F100GADNA, R5F100GCDNA, R5F100GDDNA, R5F100GEDNA, R5F100GFDNA, R5F100GDNA, R5F100GHDNA, R5F100GJDNA, R5F100GKDNA, R5F100GLDNA

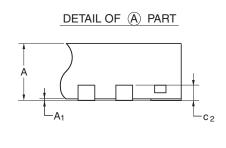
R5F101GADNA, R5F101GCDNA, R5F101GDDNA, R5F101GEDNA, R5F101GFDNA, R5F101GGDNA, R5F101GHDNA, R5F101GJDNA, R5F101GKDNA, R5F101GLDNA

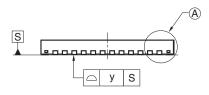
R5F100GAGNA, R5F100GCGNA, R5F100GDGNA, R5F100GEGNA, R5F100GFGNA, R5F100GHGNA, R5F100GJGNA

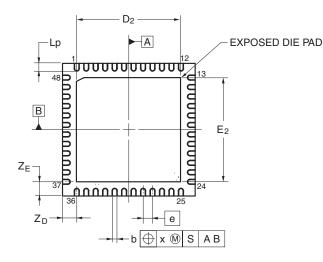
JEITA Package code	RENESAS code	Previous code	MASS(TYP.)[g]
P-HWQFN48-7x7-0.50	PWQN0048KB-A	48PJN-A P48K8-50-5B4-6	0.13











Referance	Dimension in Millimeters		
Symbol	Min	Nom	Max
D	6.95	7.00	7.05
Е	6.95	7.00	7.05
Α			0.80
A ₁	0.00		_
b	0.18	0.25	0.30
е		0.50	_
Lp	0.30	0.40	0.50
Х			0.05
у			0.05
Z _D		0.75	_
Z _E		0.75	
C ₂	0.15	0.20	0.25
D ₂		5.50	_
E ₂		5.50	_

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R5F100LCAFB, R5F100LDAFB, R5F100LEAFB, R5F100LFAFB, R5F100LGAFB, R5F100LHAFB, R5F100LJAFB, R5F100LKAFB, R5F100LLAFB

R5F101LCAFB, R5F101LDAFB, R5F101LEAFB, R5F101LFAFB, R5F101LGAFB, R5F101LHAFB,

R5F101LJAFB, R5F101LKAFB, R5F101LLAFB

R5F100LCDFB, R5F100LDDFB, R5F100LEDFB, R5F100LFDFB, R5F100LGDFB, R5F100LHDFB, R5F100LDFB, R5F100LKDFB, R5F100LKDFB

R5F101LCDFB, R5F101LDDFB, R5F101LEDFB, R5F101LFDFB, R5F101LGDFB, R5F101LHDFB,

R5F101LJDFB, R5F101LKDFB, R5F101LLDFB

R5F100LCGFB, R5F100LDGFB, R5F100LEGFB, R5F100LFGFB, R5F100LGGFB, R5F100LHGFB, R5F100LJGFB

	JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.)) [g]
	P-LFQFP64-10x10-0.50	PLQP0064KF-A	P64GB-50-UEU-2	0.35	
	HD — D — 48 49	33	E HE	detail of	lead end
E -	64 1 1 -ZD	17 16 e		ITEM D E HD HE A	(UNIT:mm) DIMENSIONS 10.00±0.20 10.00±0.20 12.00±0.20 12.00±0.20 160 MAX. 0.10±0.05
Œ	- b	x (M) S	A2 ¬	A2 A3 b c L Lp	1.40±0.05 0.25 0.22±0.05 0.145 +0.055 0.50 0.60±0.15
<u> </u>	Lays		A1	L1 θ e x	1.00±0.20 3°+5° 0.50 0.08

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0.08

1.25

ZD

ZΕ

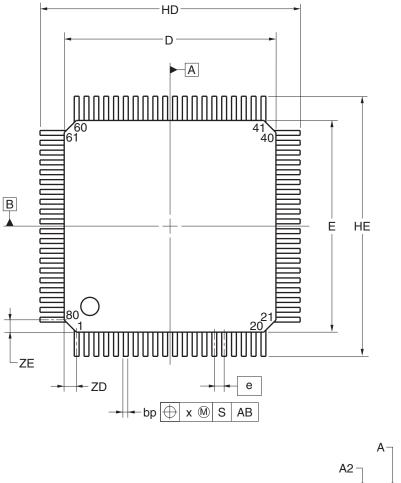
NOTE

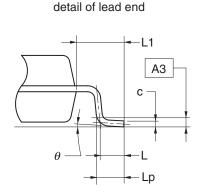
Each lead centerline is located within 0.08 mm of its true position at maximum material condition.

4.12 80-pin Products

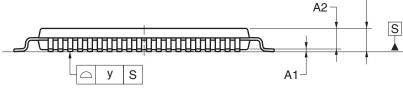
R5F100MFAFA, R5F100MGAFA, R5F100MHAFA, R5F100MJAFA, R5F100MKAFA, R5F100MLAFA R5F101MFAFA, R5F101MGAFA, R5F101MHAFA, R5F101MJAFA, R5F101MKAFA, R5F101MLAFA R5F100MFDFA, R5F100MGDFA, R5F100MHDFA, R5F100MJDFA, R5F100MKDFA, R5F101MLDFA R5F101MFDFA, R5F101MGDFA, R5F101MHDFA, R5F101MJDFA, R5F101MKDFA, R5F101MLDFA R5F100MFGFA, R5F100MGGFA, R5F100MHGFA, R5F100MJGFA

JEITA Package Code	RENESAS Code	Previous Code	MASS (TYP.) [g]
P-LQFP80-14x14-0.65	PLQP0080JB-E	P80GC-65-UBT-2	0.69





Referance	Dimension in Millimeters			
Symbol	Min Nom		Max	
D	13.80	14.00	14.20	
Е	13.80	14.00	14.20	
HD	17.00	17.20	17.40	
HE	17.00	17.20	17.40	
А			1.70	
A1	0.05	0.125	0.20	
A2	1.35	1.40	1.45	
A3		0.25		
bp	0.26	0.32	0.38	
С	0.10	0.145	0.20	
L		0.80		
Lp	0.736	0.886	1.036	
L1	1.40	1.60	1.80	
θ	0°	3°	8°	
е		0.65		
х	х —		0.13	
У	у — —		0.10	
ZD		0.825		
ZE	ZE —			



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RL78/G13 Data Sheet

			Description	
Rev.	Date	Page	Summary	
1.00	Feb 29, 2012	-	First Edition issued	
2.00	Oct 12, 2012	7	Figure 1-1. Part Number, Memory Size, and Package of RL78/G13: Pin count	
			corrected.	
		25	1.4 Pin Identification: Description of pins INTP0 to INTP11 corrected.	
		40, 42, 44	1.6 Outline of Functions: Descriptions of Subsystem clock, Low-speed on-chip oscillator, and General-purpose register corrected.	
		41, 43, 45	1.6 Outline of Functions: Lists of Descriptions changed.	
		59, 63, 67	Descriptions of Note 8 in a table corrected.	
		68	(4) Common to RL78/G13 all products: Descriptions of Notes corrected.	
		69	2.4 AC Characteristics: Symbol of external system clock frequency corrected.	
		96 to 98	2.6.1 A/D converter characteristics: Notes of overall error corrected.	
		100	2.6.2 Temperature sensor characteristics: Parameter name corrected.	
		104	2.8 Flash Memory Programming Characteristics: Incorrect descriptions corrected.	
		116	3.10 52-pin products: Package drawings of 52-pin products corrected.	
		120	3.12 80-pin products: Package drawings of 80-pin products corrected.	
3.00	Aug 02, 2013	1	Modification of 1.1 Features	
		3	Modification of 1.2 List of Part Numbers	
		4 to 15	Modification of Table 1-1. List of Ordering Part Numbers, note, and caution	
		16 to 32	Modification of package type in 1.3.1 to 1.3.14	
		33	Modification of description in 1.4 Pin Identification	
		48, 50, 52	Modification of caution, table, and note in 1.6 Outline of Functions	
		55	Modification of description in table of Absolute Maximum Ratings (T _A = 25°C)	
		57	Modification of table, note, caution, and remark in 2.2.1 X1, XT1 oscillator characteristics	
		57	Modification of table in 2.2.2 On-chip oscillator characteristics	
		58	Modification of note 3 of table (1/5) in 2.3.1 Pin characteristics	
		59	Modification of note 3 of table (2/5) in 2.3.1 Pin characteristics	
		63	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		64	Modification of notes 1 and 4 in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		65	Modification of table in (1) Flash ROM: 16 to 64 KB of 20- to 64-pin products	
		66	Modification of notes 1, 5, and 6 in (1) Flash ROM: 16 to 64 KB of 20- to 64-	
		68	pin products Modification of notes 1 and 4 in (2) Flash ROM: 96 to 256 KB of 30- to 100-	
		70	pin products Modification of notes 1, 5, and 6 in (2) Flash ROM: 96 to 256 KB of 30- to	
		72	100-pin products Modification of notes 1 and 4 in (3) Flash ROM: 384 to 512 KB of 44- to 100-	
			pin products	
		74	Modification of notes 1, 5, and 6 in (3) Flash ROM: 384 to 512 KB of 44- to 100-pin products	
		75	Modification of (4) Peripheral Functions (Common to all products)	
		77	Modification of table in 2.4 AC Characteristics	
		78, 79	Addition of Minimum Instruction Execution Time during Main System Clock Operation	
		80	Modification of figures of AC Timing Test Points and External System Clock Timing	